



Session Title:	[WeB1] UV Devices
Session Date:	July 15 (Wed.), 2026
Session Time:	10:25-12:10
Session Room:	Room B (Baekrok Hall B-2, 1F)
Session Chairs	

[WeB1-1] [Invited]	10:25-10:55
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TBA

Tim Wernicke, Technische Universität Berlin, Germany

[WeB1-2] [Invited]	10:55-11:25
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MOVPE Growth of UV-B Laser Diodes on Sapphire Substrate and Realization of Room-Temperature Continuous-Wave Operation

Motoaki Iwaya, Takumu Saito, Rintaro Miyake, Sho Iwayama, Tetsuya Takeuchi, Satoshi Kamiyama, and Hideto Miyake, Meijo University, Japan

[WeB1-3]	11:25-11:40
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Low-Leakage Shallow-Beveled Mesa GaN Ultraviolet Avalanche Photodiodes with AlGaIn Windows for Improved Responsivity

Davide Balzerani¹, Alexandra V. Dolgashev¹, A. Nepomuk Otte¹, Theeradetch Detchprohm¹, Subhra Chowdhury², Dhruvas Biswas², and Russell D. Dupuis¹, ¹Georgia Institute of Technology, USA, ²Magnolia Optical Technologies, USA

[WeB1-4]	11:40-11:55
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MOVPE-Grown p-AlGaIn with Coupled Polarization and Impurity Doping Achieving 12% EQE in Deep-Ultraviolet LEDs

Hongyu Liu¹, Li Chen², Jichun Ye¹, and Wei Guo¹, ¹Ningbo Institute of Materials Technology and Engineering, Chinese Academy of Science, China, ²Yongjiang Laboratory, China

[WeB1-5]	11:55-12:10
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Nanoscale Characterization of Carrier Capture into the Active Region of Far-UVC LEDs

Frank Bertram¹, Gordon Schmidt¹, Niklas Dreyer¹, Peter Veit¹, Jürgen Christen¹, M. Ajmal Khan², Kohel Fujimoto^{2,3}, M. Nawaz Sharif^{2,3}, Hiroyuki Yaguchi³, and Hideki Hirayama², ¹Otto-von-Guericke University Magdeburg, Germany, ²RIKEN Cluster for Pioneering Research, Japan, ³Saitama University, Japan